

ZXMP6A17KTC Datasheet

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DiGi Electronics Part Number	ZXMP6A17KTC-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	ZXMP6A17KTC
Description	MOSFET P-CH 60V 4.4A TO252-3
Detailed Description	P-Channel 60 V 4.4A (Ta) 2.11W (Ta) Surface Moun t TO-252-3

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
ZXMP6A17KTC	Diodes Incorporated
Series:	Product Status:
	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
60 V	4.4A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
4.5V, 10V	125mOhm @ 2.3A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
1V @ 250μA	17.7 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	637 pF @ 30 V
FET Feature:	Power Dissipation (Max):
-	2.11W (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
TO-252-3	TO-252-3, DPAK (2 Leads + Tab), SC-63
Base Product Number:	
ZXMP6A17	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	







ZXMP6A17K

60V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = 25°C
-60V	125mΩ @ V _{GS} = -10V	-6.6A
	190mΩ @ V _{GS} = -4.5V	-5.3A

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- DC-DC Converters
- Power management functions

Features and Benefits

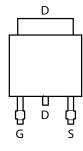
- Low on-resistance
- Fast switching speed
- "Green" component and RoHS compliant (Note 1)

Mechanical Data

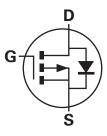
- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)



Top View



Pin Out -Top View



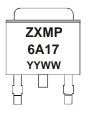
Equivalent Circuit

Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP6A17KTC	See Below	13	16	2,500

Note: 1. Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

Marking Information



ZXMP = Product Type Marking Code, Line 1 6A17 = Product Type Marking Code, Line 2 YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01-52)





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit	
Drain-Source voltage			V _{DSS}	-60	V	
Gate-Source voltage			V _{GS}	±20	V	
		(Note 3)		6.6		
Continuous Drain current	$V_{GS} = 10V$	T _A =70°C (Note 3)	I _D	5.3	А	
		(Note 2)		4.4		
Pulsed Drain current	V _{GS} = 10V	(Note 4)	I _{DM}	20.3	А	
Continuous Source current (Body diode) (Note 3)		(Note 3)	Is	9.3	А	
Pulsed Source current (Body diode) (Note 4)		I _{SM}	20.3	А		

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
	(Note 2)		4.17 33.3		
Power dissipation Linear derating factor	(Note 3)	PD	9.25 74.0	₩ mW/°C	
	(Note 5)		2.11 16.8		
	(Note 2)		30.0		
Thermal Resistance, Junction to Ambient	(Note 3)	$R_{ ext{ heta}}JA$	13.5	- -	
	(Note 5)		59.1	°C/W	
Thermal Resistance, Junction to Lead	(Note 6)	R ₀ JL	2.41		
Operating and storage temperature range		TJ, T _{STG}	-55 to 150	۵°	

2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is Notes: measured when operating in a steady-state condition.

3. Same as note 2, except the device is measured at t \leq 10 sec.

4. Same as note 2, except the device is pulsed with D = 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.

5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is

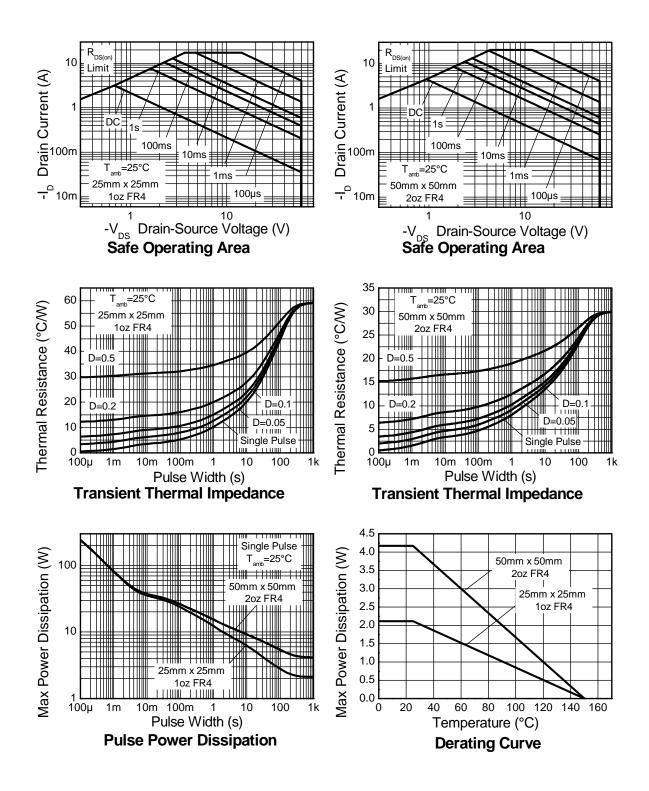
measured when operating in a steady-state condition.

6. Thermal resistance from junction to solder-point (at the end of the drain lead).





Thermal Characteristics







Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test	Condition	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	-60			V	I _D = -250μA, V _{GS} = 0V		
Zero Gate Voltage Drain Current	I _{DSS}	_		-0.5	μA	V _{DS} = -60V, V _G	s= 0V	
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS}=\pm 20V, V_{D}$	s= 0V	
ON CHARACTERISTICS								
Gate Threshold Voltage	V _{GS(th)}	-1.0		_	V	I _D = -250μA, V _D	_S = V _{GS}	
Static Drain-Source On-Resistance (Note 7)	D			0.125	Ω	V_{GS} = -10V, I_{D} =	-2.3A	
Static Drain-Source On-Resistance (Note 7)	R _{DS} (ON)	_		0.190	12	V_{GS} = -4.5V, I_{D} =	= -1.9A	
Forward Transconductance (Notes 7 & 8)	g fs	_	4.7	—	S	V _{DS} = -15V, I _D =	-2.2A	
Diode Forward Voltage (Note 7)	V _{SD}	_	-0.85	-0.95	V	I _S = -2A, V _{GS} = 0V		
Reverse recovery time (Note 8)	t _{rr}		25.1	—	ns	—I _S = -1.7A, di/dt= 100A/μs		
Reverse recovery charge (Note 8)	Q _{rr}	_	27.2	—	nC			
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	C _{iss}	_	637		pF		a) /	
Output Capacitance	C _{oss}	_	70		pF	− V _{DS} = -30V, V _G f= 1MHz	_S = 0V	
Reverse Transfer Capacitance	Crss	_	53		pF			
Total Gate Charge	Qg	_	9.0		nC	V _{GS} = -4.5V		
Total Gate Charge	Qg		17.7		nC		V _{DS} = -30V	
Gate-Source Charge	Q _{gs}	_	1.6		nC	V _{GS} = -10V	I _D = -2.2A	
Gate-Drain Charge	Q _{gd}	_	4.4		nC	1		
Turn-On Delay Time (Note 9)	t _{D(on)}	_	2.6		ns		•	
Turn-On Rise Time (Note 9)	tr	_	3.4		ns	V _{DD} = -30V, V _{GS} = -10V		
Turn-Off Delay Time (Note 9)	t _{D(off)}	_	26.2		ns	I _D = -1A, R _G ≅ 6	.0Ω	
Turn-Off Fall Time (Note 9)	t _f	_	11.3		ns	1		

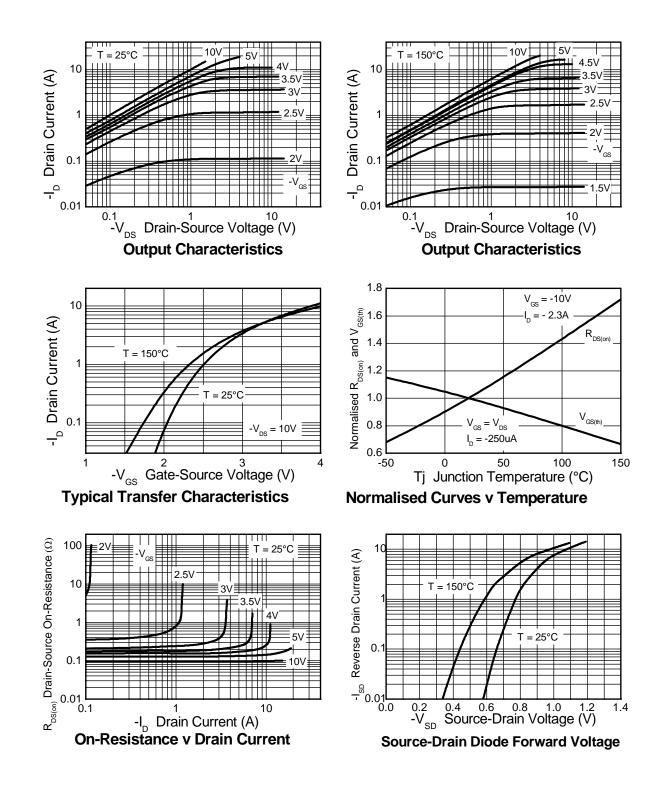
Notes:

Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%
For design aid only, not subject to production testing.
Switching characteristics are independent of operating junction temperatures.





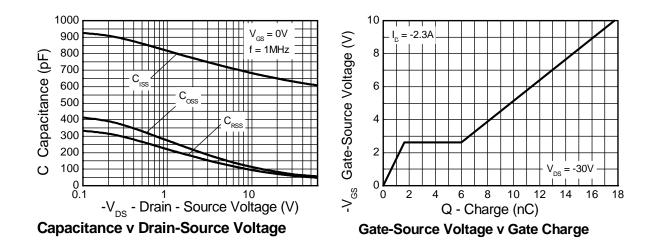
Typical Characteristics



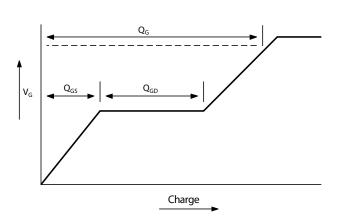




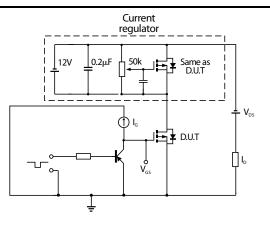
Typical Characteristics - continued



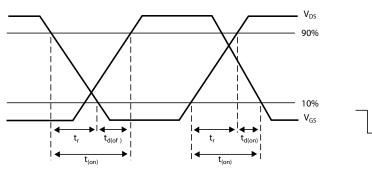
Test Circuits



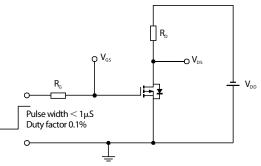
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

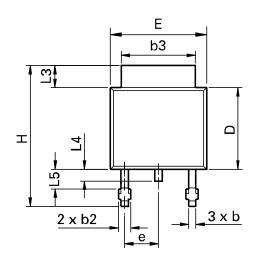


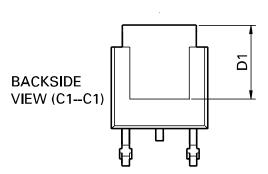
Switching time test circuit

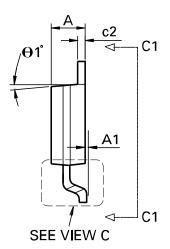


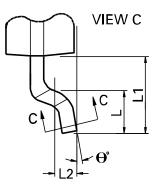


Package Outline Dimensions







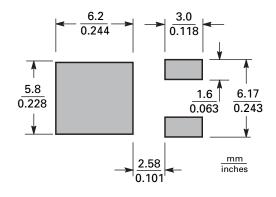


DIM	Inc	hes	Millin	neters	DIM	Inc	hes	Millim	neters
	Min	Max	Min	Max		Min	Max	Min	Max
А	0.086	0.094	2.18	2.39	е	0.090) BSC	2.29	BSC
A1	-	0.005	-	0.127	н	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
с	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
Е	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-





Suggested Pad Layout



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